

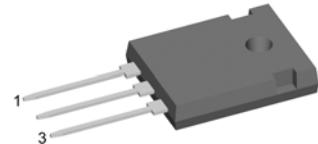
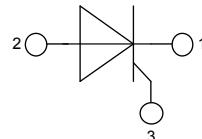
High Efficiency Thyristor

Single Thyristor

$V_{RRM} = 1200 \text{ V}$
 $I_{T(AV)M} = 30 \text{ A}$
 $I_{T(RMS)} = 47 \text{ A}$

Part number

CLA 30 E 1200 HB



Backside: anode

Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

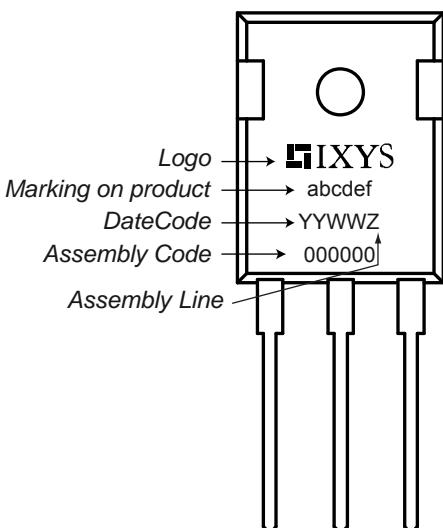
Package:

- Housing: TO-247
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ\text{C}$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ\text{C}$			1200	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1200 \text{ V}$ $V_{R/D} = 1200 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		10 2	μA mA
V_T	forward voltage drop	$I_T = 30 \text{ A}$ $I_T = 60 \text{ A}$ $I_T = 30 \text{ A}$ $I_T = 60 \text{ A}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		1.28 1.56 1.25 1.61	V
$I_{T(AV)M}$	average forward current	$T_C = 120^\circ\text{C}$	$T_{VJ} = 150^\circ\text{C}$		30	A
$I_{T(RMS)}$	RMS forward current	180° sine	$T_{VJ} = 150^\circ\text{C}$		47	A
V_{TO} r_T	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		0.86 12.5	V $\text{m}\Omega$
R_{thJC}	thermal resistance junction to case				0.55	K/W
T_{VJ}	virtual junction temperature			-40	150	$^\circ\text{C}$
P_{tot}	total power dissipation		$T_C = 25^\circ\text{C}$		190	W
P_{GM}	max. gate power dissipation	$t_p = 30 \mu\text{s}$ $t_p = 300 \mu\text{s}$	$T_C = 150^\circ\text{C}$		10 5 0.5	W
P_{GAV}	average gate power dissipation					W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0 \text{ V}$ $T_{VJ} = 150^\circ\text{C}$ $V_R = 0 \text{ V}$		300 325 255 275	A
I^{2t}	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0 \text{ V}$ $T_{VJ} = 150^\circ\text{C}$ $V_R = 0 \text{ V}$		450 440 325 315	A^2s
C_J	junction capacitance	$V_R = 400 \text{ V}$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$	13		pF

		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^\circ C$ repetitive, $I_T = 40 A$ $f = 50 Hz$; $t_p = 200 \mu s$ $I = 0.3 A$; $di/dt = 0.3 A/\mu s$			150	A/ μs
		$V_D = \frac{2}{3} V_{DRM}$ non-repetitive, $I_T = 30 A$			500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 150^\circ C$ $R_{GK} = \infty$; method 1 (linear voltage rise)			500	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6 V$ $T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$			1.3	V
I_{GT}	gate trigger current	$V_D = 6 V$ $T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$			28	mA
I_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 150^\circ C$			0.2	V
I_{GD}	gate non-trigger current				1	mA
I_L	latching current	$t_p = 10 \mu s$ $T_{VJ} = 25^\circ C$ $I = 0.3 A$; $di/dt = 0.3 A/\mu s$			90	mA
I_H	holding current	$V_D = 6 V$ $R_{GK} = \infty$ $T_{VJ} = 25^\circ C$			60	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$ $T_{VJ} = 25^\circ C$ $I = 0.3 A$; $di/dt = 0.3 A/\mu s$			2	μs
t_q	turn-off time	$V_R = 100 V$; $I_T = 30 A$ $T_{VJ} = 150^\circ C$ $V_D = \frac{2}{3} V_{DRM}$; $t_p = 200 \mu s$ $di/dt = 10 A/\mu s$; $dv/dt = 20 V/\mu s$		150		μs

Symbol	Definition	Conditions	Ratings		
			min.	typ.	max.
I_{RMS}	RMS current	per terminal		50	A
R_{thCH}	thermal resistance case to heatsink			0.25	K/W
T_{stg}	storage temperature		-55		150 °C
Weight				6	g
M_D	mounting torque		0.8		1.2 Nm
F_c	mounting force with clip		20		120 N

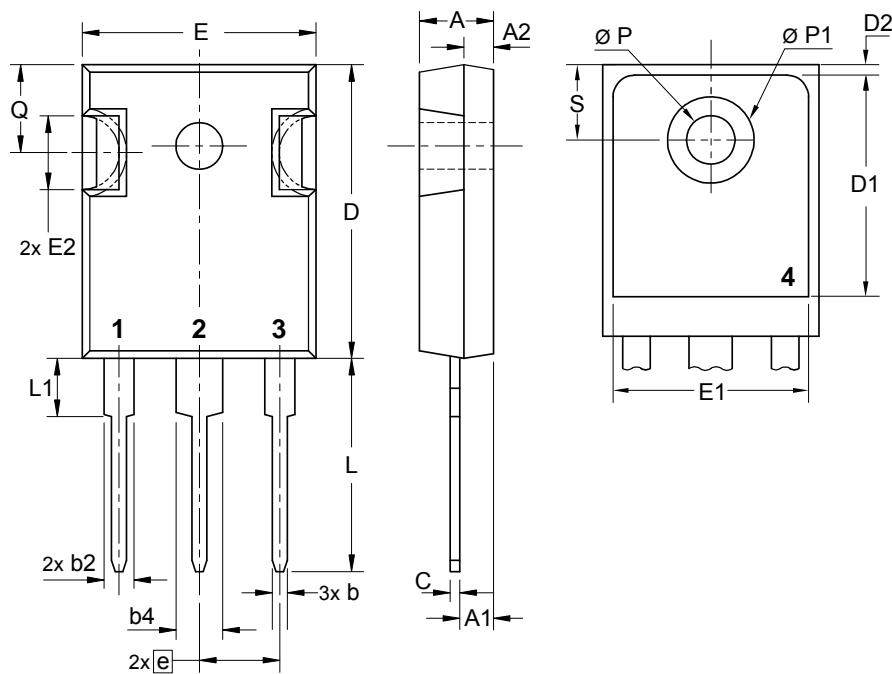
Part number**Product Marking**

C = Thyristor (SCR)
 L = High Efficiency Thyristor
 A = (up to 1200 V)
 30 = Current Rating [A]
 E = Single Part
 1200 = Reverse Voltage [V]
 HB = TO-247AD (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	CLA 30 E 1200 HB	CLA30E1200HB	Tube	30	508221

Similar Part	Package	Voltage class
CLA30E1200PB	TO-220AB (3)	1200
CLA30E1200PC	TO-263AB (D2Pak)	1200
CS22-12io1M	TO-220ABFP (3)	1200
CS22-08io1M	TO-220ABFP (3)	800
CMA30E1600PN	TO-220ABFP (3)	1600
CMA30E1600PB	TO-220AB (3)	1600

Outlines TO-247



Sym.	Inches min. max.	Millimeter min. max.
A	0.185 0.209	4.70 5.30
A1	0.087 0.102	2.21 2.59
A2	0.059 0.098	1.50 2.49
D	0.819 0.845	20.79 21.45
E	0.610 0.640	15.48 16.24
E2	0.170 0.216	4.31 5.48
e	0.215 BSC	5.46 BSC
L	0.780 0.800	19.80 20.30
L1	- 0.177	- 4.49
Ø P	0.140 0.144	3.55 3.65
Q	0.212 0.244	5.38 6.19
S	0.242 BSC	6.14 BSC
b	0.039 0.055	0.99 1.40
b2	0.065 0.094	1.65 2.39
b4	0.102 0.135	2.59 3.43
c	0.015 0.035	0.38 0.89
D1	0.515 -	13.07 -
D2	0.020 0.053	0.51 1.35
E1	0.530 -	13.45 -
Ø P1	- 0.29	- 7.39

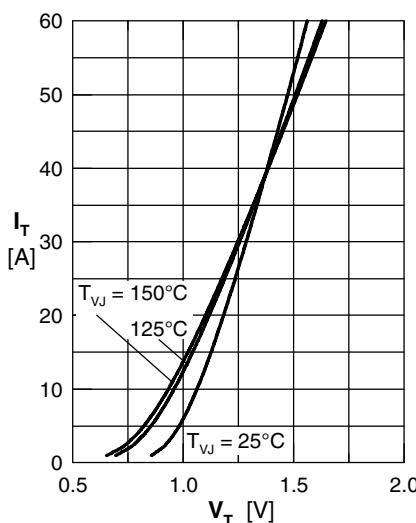


Fig. 1 Forward characteristics

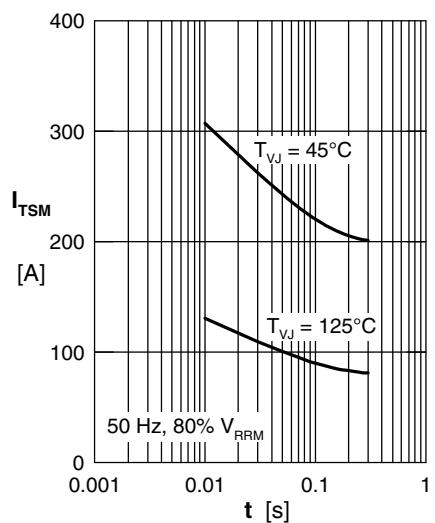
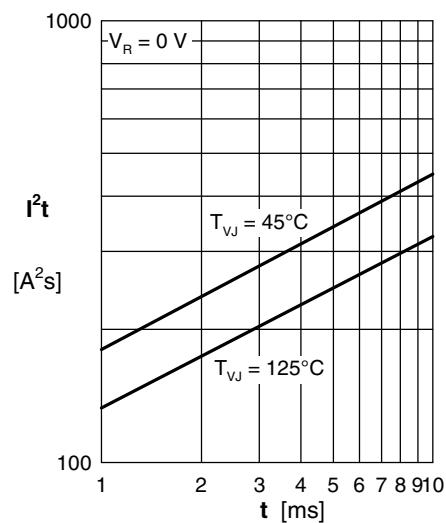
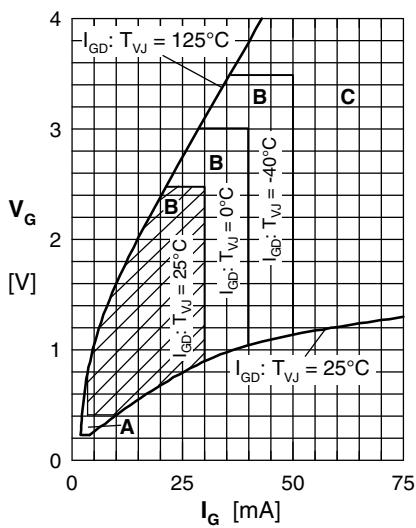
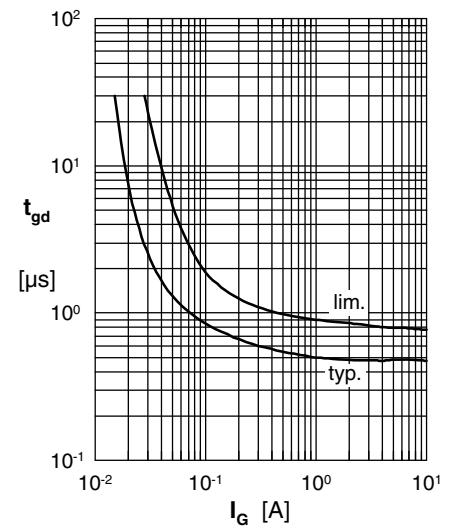
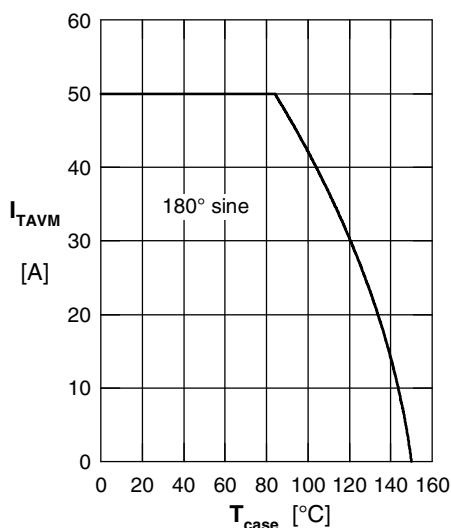
Fig. 2 Surge overload current
 I_{TSM} : crest value, t : durationFig. 3 I^2t versus time (1-10 s)Fig. 4 Gate voltage & gate current
Triggering: A = no; B = possible; C = safeFig. 5 Gate controlled delay time t_{gd} 

Fig. 6 Max. forward current at case temperature

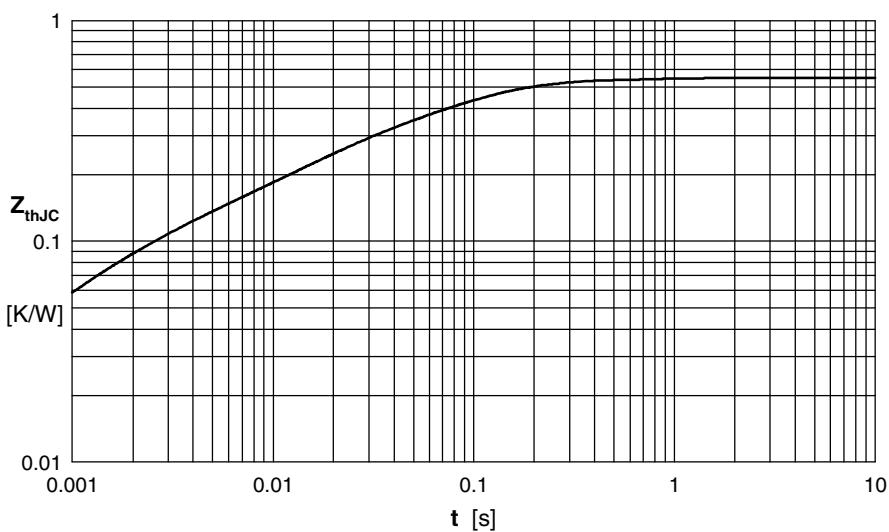


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.024	0.0005
2	0.059	0.0018
3	0.128	0.014
4	0.306	0.08
5	0.033	0.56